

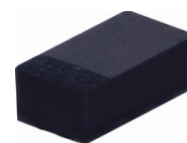
SMD Switching Diode



SMD Diodes Specialist

CDSF355B (RoHs Device)

High Speed



Features

Designed for mounting on small surface.

Extremely thin/leadless package.

Low leakage current.

High mounting capability, strong surge withstand, high reliability.

Mechanical data

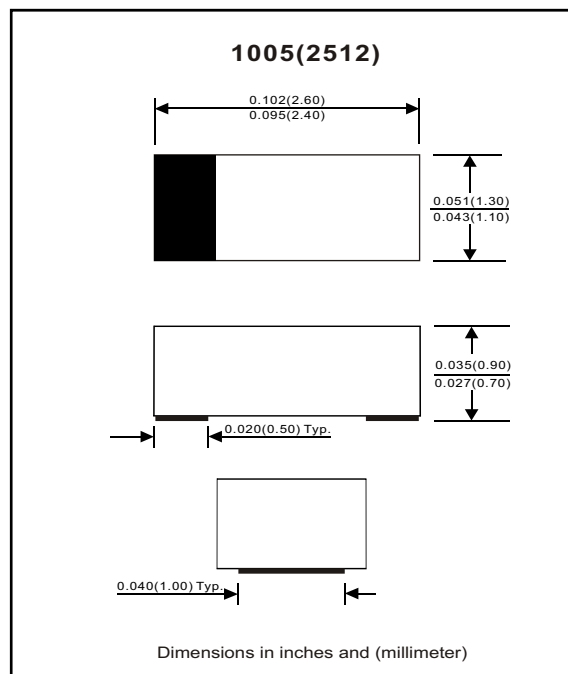
Case: 1005(2512) standard package, molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.006 gram(approx.).



www.DataSheet4U.com

Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			90	V
Reverse voltage		V_R			80	V
Average forward current		I_O			100	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}		1000		mA
Repetitive peak forward current		I_{FRM}			225	mA
Power Dissipation		P_D			300	mW
Storage temperature		T_{STG}	-55		+125	°C
Junction temperature		T_j			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100$ mA DC	V_F			1.0	V
Reverse current	$V_R = 80$ V	I_R			0.1	uA
Capacitance between terminals	$f = 1$ MHz, and 0.5VDC reverse voltage	C_T			3	pF
Reverse recovery time	$V_R = 6$ V , $I_F = 10$ mA, $R_L = 50$ ohms	T_{rr}			4	nS

REV:B

RATING AND CHARACTERISTIC CURVES (CDSF355B)

Fig. 1 - Forward characteristics

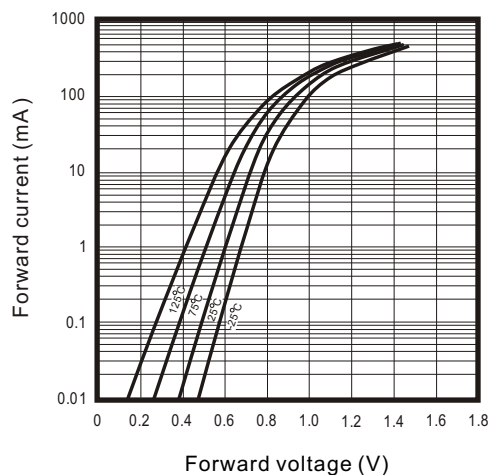


Fig. 2 - Reverse characteristics

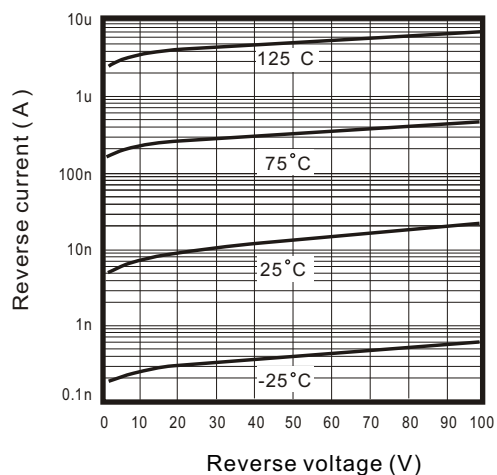


Fig. 3 - Capacitance between terminals characteristics

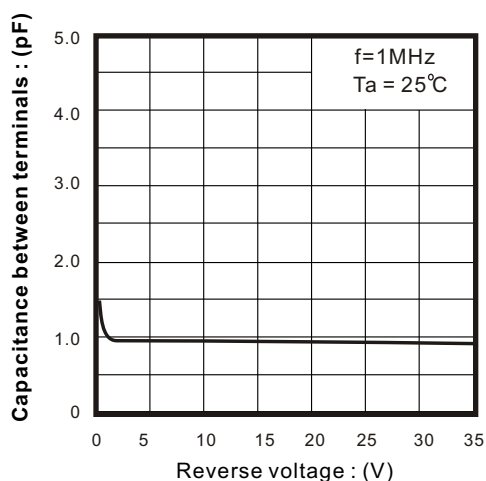


Fig. 4 - Current derating curve

